

General Description

The WSR2N65 is the highest performance trench N-Ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WSR2N65 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent Cdv/dt effect decline
- Green Device Available

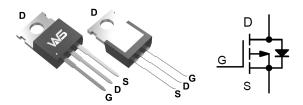
Product Summery

BV _{DSS}	R _{DSON}	I _D
650V	4.8Ω	2A

Applications

- AC/DC Power Conversion in Switched Mode Power Supplies (SMPS).
- Uninterruptible Power Supply(UPS)
- Adapter.

TO-220 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units	
V_{DS}	Drain-Source Voltage	650	V	
V_{GS}	Gate-Source Voltage	±30	V	
I _D @T _C =25℃	Continuous Drain Current, V _{GS} @ 10V ^{1.5}	2	Α	
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ 10V ^{1.5}	1	Α	
I _{DM}	Pulsed Drain Current ^{1.2.5}	6	А	
EAS	Single Pulse Avalanche Energy ¹	57	mJ	
P _D	Total Power Dissipation ^{1,5}	25	W	
T _{STG}	Storage Temperature Range	-55 to 150	$^{\circ}$	
T_J	Operating Junction Temperature Range	-55 to 150	${\mathbb C}$	

Thermal Data

Symbol	Parameter	Тур.	Max.	Unit
R _{0JA}	Thermal Resistance Junction-ambient ¹		62.5	°C/W
$R_{ heta JC}$	Thermal Resistance Junction-Case ¹		5	°C/W



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	650			V
$\triangle BV_{DSS}/\triangle T_{J}$	BVDSS Temperature Coefficient	Reference to 25℃ , I _D =250uA		0.6		V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V , I _D =1A		4.0	4.8	Ω
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} . In =250uA	2.0	3.0	4.0	V
$ riangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	VGS-VDS, ID -250UA		-4.57		mV/℃
	Drain-Source Leakage Current	V_{DS} =650V , V_{GS} =0V , T_J =25 $^{\circ}$ C			1	- uA
I _{DSS}		V_{DS} =520V , V_{GS} =0V , T_J =55 $^{\circ}$ C			10	
I _{GSS}	Gate-Source Leakage Current	V_{GS} = $\pm30V$, V_{DS} = $0V$			±100	nA
gfs	Forward Transconductance	V _{DS} =300V , I _D =1A		5		S
Q_g	Total Gate Charge (10V)			8.0		nC
Q _{gs}	Gate-Source Charge	V _{DS} =520V , V _{GS} =10V , I _D =1A		1.2		
Q _{gd}	Gate-Drain Charge			5		
T _{d(on)}	Turn-On Delay Time	V_{DD} =300V , V_{GS} =10V , R_{G} =25 Ω , I_{D} =1A.		7.8		
Tr	Rise Time			33]
T _{d(off)}	Turn-Off Delay Time			23		ns
T_f	Fall Time			59		
C _{iss}	Input Capacitance	V _{DS} =25V , V _{GS} =0V , f=1MHz		310		
Coss	Output Capacitance			39		pF
C _{rss}	Reverse Transfer Capacitance			6		

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current ^{1,2,5}	V =V =0V Force Current			2	Α
I _{SM}	Pulsed Source Current ^{1,2}	V _G =V _D =0V , Force Current			6	Α
V _{SD}	Diode Forward Voltage ¹	V _{GS} =0V , I _S =2A , T _J =25℃			1.4	V
t _{rr}	Reverse Recovery Time			80		nS
Qrr	Reverse Recovery Charge	lF=2A , dl/dt=100A/μs		1800		nC

Notes:

Note 1 : limited by maximum junction temperature.

Note 2: Bond wire current limit. Note 3: V_{DS}=520V, I_D=2A.

Note 4 : $I_D=1A$, $V_{DD}=50V$, $T_i=25$ °C.

Note 5: Repetitive Rating : Pulse width limited by maximum junction temperature.



Typical Characteristics

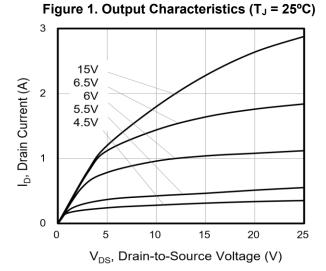


Figure 3. Drain Current vs. Temperature

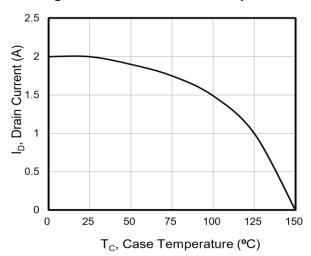


Figure 5. Transfer Characteristics

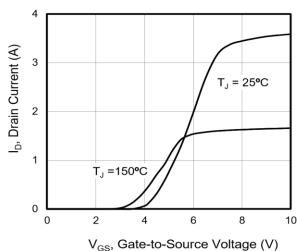
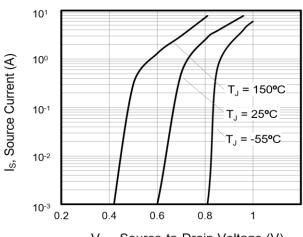


Figure 2. Body Diode Forward Voltage



V_{SD}, Source-to-Drain Voltage (V)

Figure 4. Power Dissipation vs. Temperature

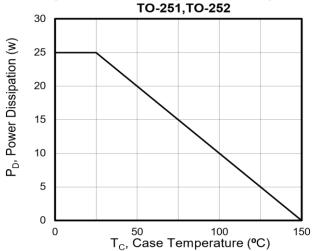
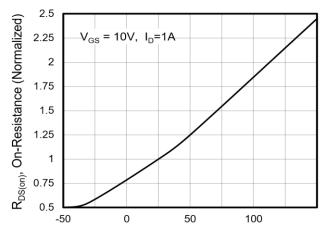


Figure 6. On-Resistance vs. Temperature

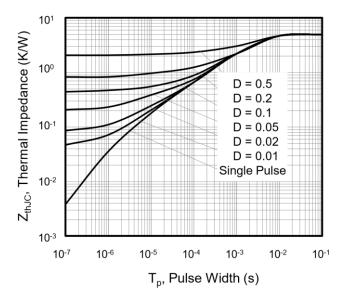


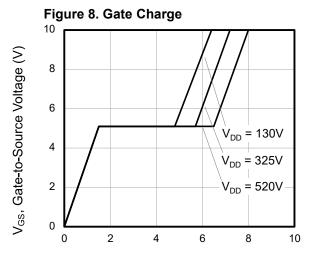
T_J, Junction Temperature (°C)



Typical Characteristics

 $V_{\text{DS}},$ Drain-to-Source Voltage (V) Figure 9. Transient Thermal Impedance





Q_g, Total Gate Charge (nC)



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STF5N65M6 IRF40H233XTMA1 STU5N65M6 DMN6022SSD-13 DMN13M9UCA6-7 DMTH10H4M6SPS-13 DMN2990UFB-7B
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